

1/1 DWPX - (C) The Thomson Corp.

AN - 2001-400886 [43]

TI - Rinsing liquid used for manufacturing of a semiconductor element or a liquid crystal panel e.g. IC, includes at least one hydroxylamine

PA - (TOKQ) TOKYO OHKA KOGYO CO LTD

IN - KOBAYASHI M; TANABE M; WAKIYA K

PN - **JP2001033988** A 20010209 DW2001-43 G03F-007/42 Jpn 10p *
AP: 1999JP-0202077 19990715

PR - 1999JP-0202077 19990715

AB - JP2001033988 A

NOVELTY: A rinsing liquid for photolithography is used for a rinsing process to be executed after the residue of the etching of a substrate while using a photoresist pattern formed on the substrate as a mask, is removed by a separation liquid, has pH 8 - 12.

- DESCRIPTION: The rinsing liquid includes at least one of hydroxylamine, and amine of which acid dissociation constant (pKa) in an aqueous solution of 25 degreesC is 7.5 - 13. The hydroxylamine is represented by a formula (I). At least hydroxylamine (NH₂OH) is included. The ammonia water is further blended in the rinsing liquid. N(R₁)(R₂)-OH (I) R₁, R₂ = respectively hydrogen atom, 1-6C lower alkyl group.

- USE: Effectively used for the manufacturing of a semiconductor element or a liquid crystal panel such as IC, LSI and the like.

UP - 2001-43